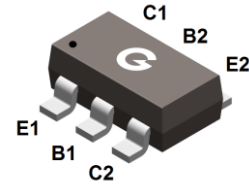
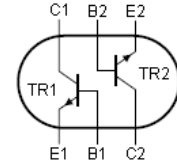


Features

- Epitaxial planar die construction
- Complimentary to BC807-6L
- High collector current
- High current gain
- Low collector-emitter saturation voltage

HF



SOT-23-6L

Mechanical Data

- Case: SOT-23-6L
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BC817-16-6L	SOT-23-6L	3000 pcs / Tape & Reel	6A
BC817-25-6L	SOT-23-6L	3000 pcs / Tape & Reel	6B•
BC817-40-6L	SOT-23-6L	3000 pcs / Tape & Reel	6C

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V _{CBO}	50	V
Collector-Emitter Breakdown Voltage	V _{CEO}	45	V
Emitter-Base Breakdown Voltage	V _{EBO}	5	V
Continuous Collector Current	I _C	0.5	A
Peak Collector Current	I _{CM}	1	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (Per transistor) *1	P _D	370	mW
Power Dissipation (Per device) *1	P _D	600	mW
Thermal Resistance Junction-to-Air *2	R _{θJA}	197	°C/W
Thermal Resistance Junction-to-Case *2	R _{θJC}	100	°C/W
Thermal Resistance Junction-to-Lead *2	R _{θJL}	29	°C/W
Operating junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	50	-	-	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	45	-	-	V
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5	-	-	V
Collector Cut-off Current		I_{CBO}	$V_{CB} = 25\text{V}, I_E = 0$	-	-	100	nA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$	-	-	100	nA
DC Current Gain	BC817-16-6L	h_{FE}	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100	-	250	-
	BC817-25-6L			160	-	400	-
	BC817-40-6L			250	-	600	-
	BC817-16-6L		$V_{CE} = 1\text{V}, I_C = 300\text{mA}$	60	-	-	-
	BC817-25-6L			100	-	-	-
	BC817-40-6L			170	-	-	-
	BC817-40-6L		$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40	-	-	-
Collector-emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	0.7	V
Base-emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	1.2	V
Transition Frequency		f_T	$I_C = 50\text{mA}, V_{CE} = 5\text{V}$ $f = 100\text{MHz}$	-	170	-	MHz
Collector Output Capacitance		C_{OBO}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	-	6	-	pF

Notes:

1. Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin plated; mounting pad for collector 1 cm^2
2. The data tested by surface mounted on a $15\text{mm} \times 15\text{mm} \times 1\text{mm}$ FR4-epoxy P.C.B

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

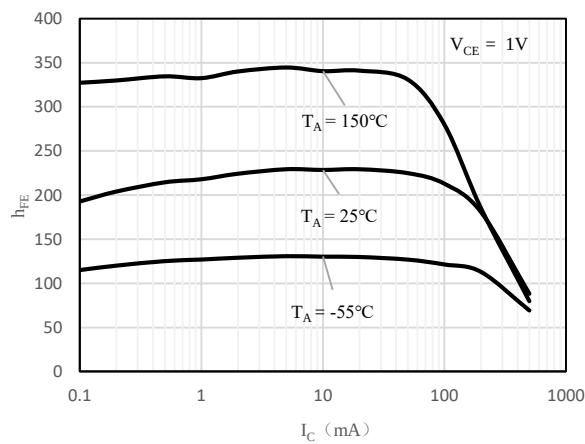


Fig 1 h_{FE} vs. I_C (BC817-16-6L)

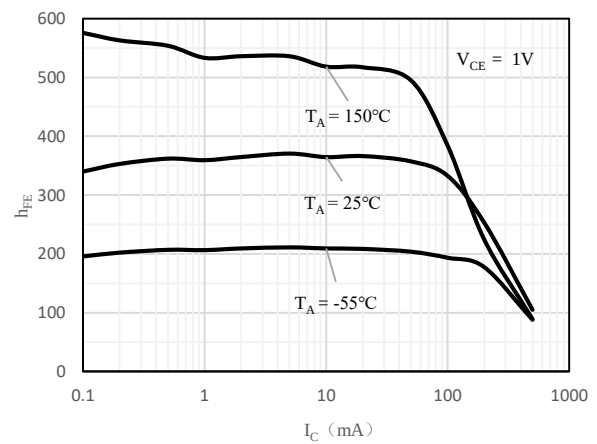


Fig 2 h_{FE} vs. I_C (BC817-25-6L)

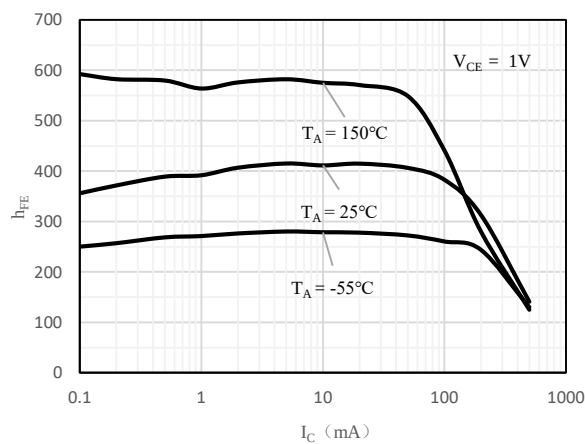


Fig 3 h_{FE} vs. I_C (BC817-40-6L)

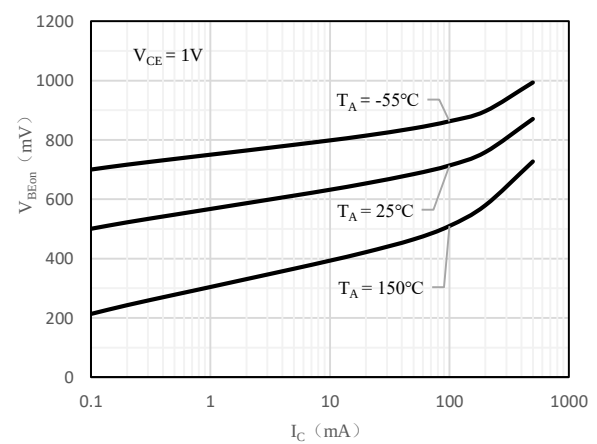


Fig 4 $V_{BE(ON)}$ vs. I_C

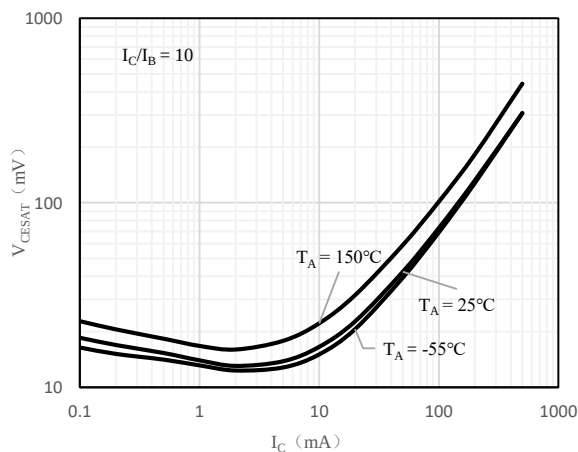


Fig 2 $V_{CE(sat)}$ vs. I_C

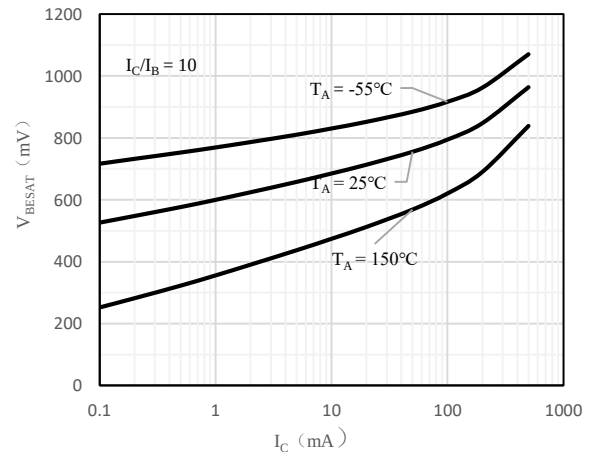
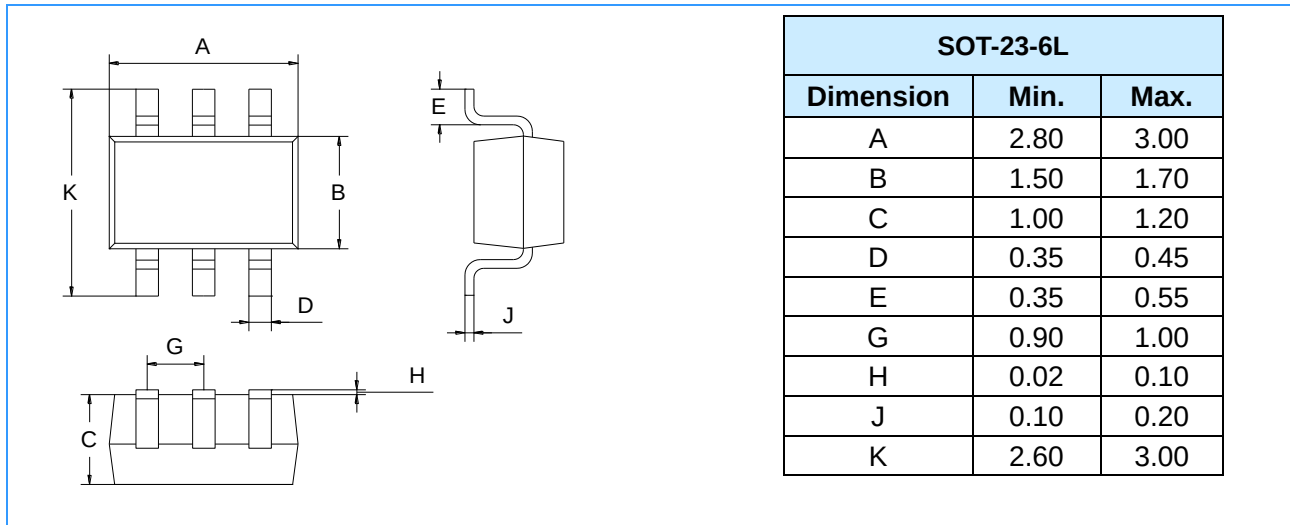
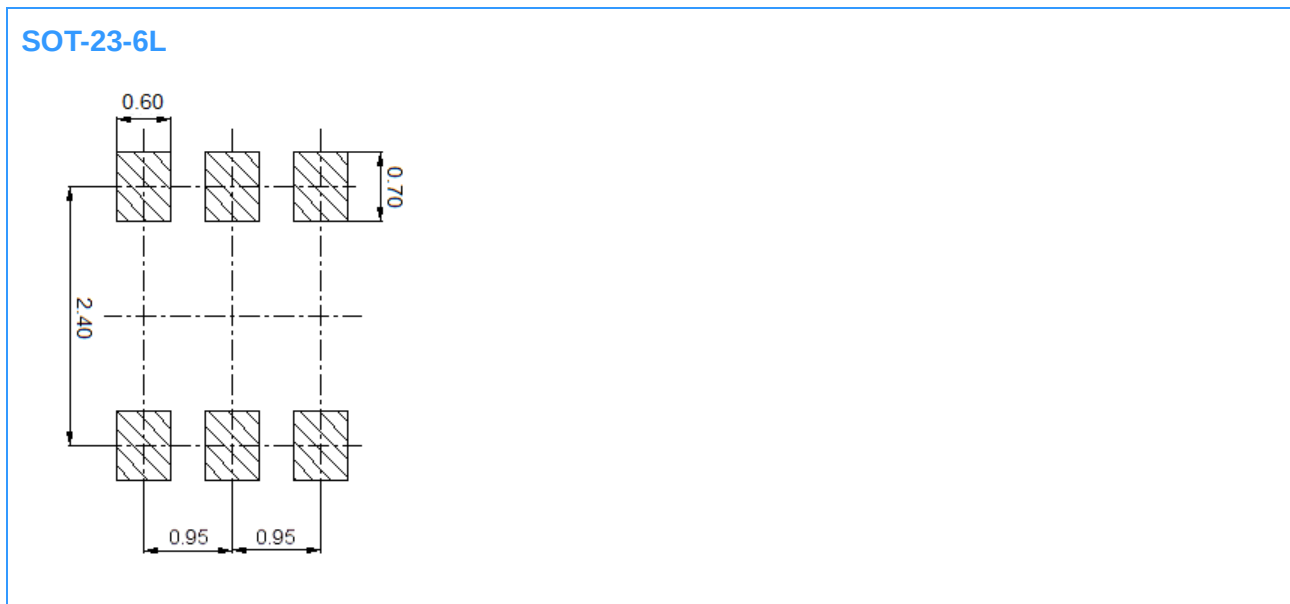


Fig 3 $V_{BE(sat)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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